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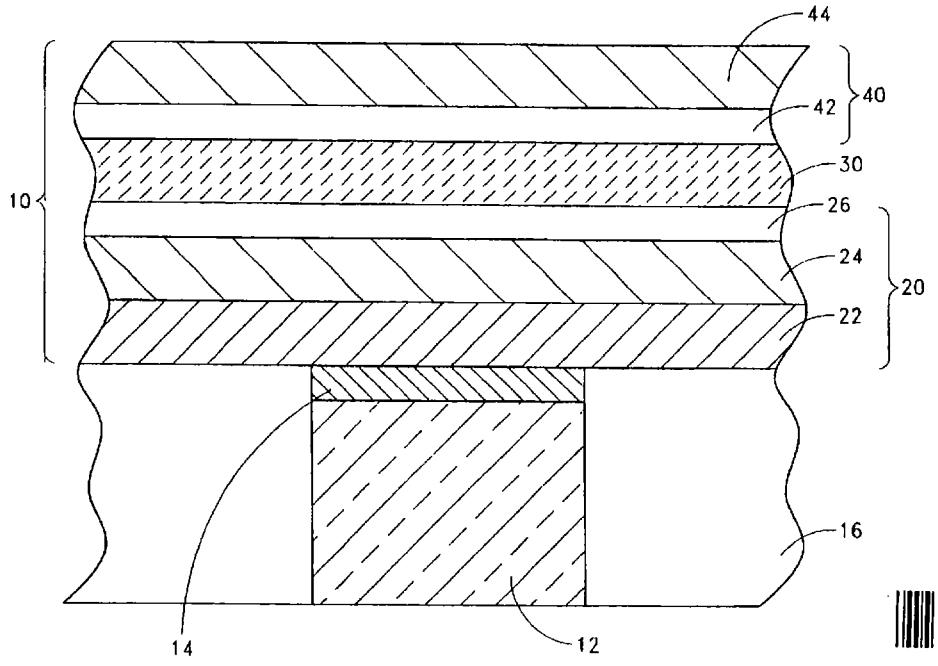
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(54) Title: RHODIUM-RICH OXYGEN BARRIERS



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(57) Abstract: Structures and methods are disclosed for forming capacitors for integrated circuits. The capacitor includes a rhodium-rich structure (24), a rhodium oxide layer (26) in direct contact with the rhodium-rich structure (24), a capacitor dielectric (30) in direct contact with the rhodium oxide layer (26) and a top electrode (40) over the capacitor. The rhodium-rich structure (24) can include rhodium alloys and the capacitor dielectric (30) preferably has a high dielectric constant.

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